

EAST: (10743814 ferro layers with different temperatures and roughness.wsp:1)

FileViewEditToolsWindowHelp

L8: (7487) afm atomic adj2 microscop\$4

L9: (552596) (rug\$4 rough\$4 asperit\$4)

L10: (675575) (non adj uniform\$4 nonuniform\$4 porous\$4 pore)

L11: (1158607) 9 10

L12: (1317) 8 with 11

L13: (15) 7 same 12

L14: (528089) nm nanometer nano adj meter angstrom

L15: (15) 13 and 14

L18: (124557) second adj (layer film)

L17: (3836) hillock

L18: (0) 18 and 7

L18: (6) 8 with 17

L20: (1162445) 11 17

L21: (2410) 16 near 20

L22: (1) 21 same 7

L23: (275291) second adj2 (layer film)

L24: (4799) 23 near 20

L25: (12) 24 same 7

L26: (7) 25 and 14

L27: (7) 26 and 20

L28: (47) 24 and 7

L28: (30487) 20 near 6 14

L30: (6) 28 and 28

L31: (2) 6864116 pn.

L12: (19) (second another upper top) adj ((ferroelectric ferro adj electric)

Failed

Browse

Queue

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Q8:

USPAT:US PGPLB:EPO:JPO:DERWENT:IDM:TDB

Plurals

Highlight all hit terms initially

Default operator:

OR

((second another upper top) adj ((ferroelectric ferro adj electric)

) near (layer film)) near 9 (temperature (rug\$4 rough\$4 asperit\$4))) 09/842631

Oct 2004

ALL term

ALL term

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	U	→	Inventor	Document#	Issue	P	Title	Current	Current	XB	Revised	S	C	P	→	→	→	→	→	→	Image Doc	P
1			Li, Tingkai et al	US 6864116	2003	7	Seed layer processes for MOCVD of ferroele	438/3													US 6864116	
2			Zhen, Wendo	US 2001004	2001	2	Semiconductor device having ferroelectric t	438/3	257/E21.01												US 2001004	
3			ZHEN, W	EP 1150344	2003	2	Manufacture of semiconductor device having														US 2001004	
4			Matsuura, Os	US 2004013	2004	1	Ferroelectric capacitor, process for producti	257/295													US 2004013	
5			Li, Tingkai et al	US 2003020	2003	8	Method of forming ferroelectric thin films on	438/3	438/763												US 2003020	
6			Li, Tingkai et al	US 2003010	2003	8	Seed layer processes for MOCVD of ferroele	438/3													US 2003010	
7			Jung, Dong-Ji	US 2002002	2002	1	Semiconductor device including ferroelectric	257/295	257/E21.02												US 2002002	
8			Shimada, Yas	US 2002002	2002	1	Semiconductor device and method for fabric	257/295	257/300												US 2002002	
9			Wikborg, Erla	US 2001005	2001	1	Electrically tunable device and a method rela	257/595	257/802												US 2001005	
10			Kawakubo, T	US 6787957	2004	1	Infrared detection element and infrared deta	250/338													US 6787957	

Ready

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